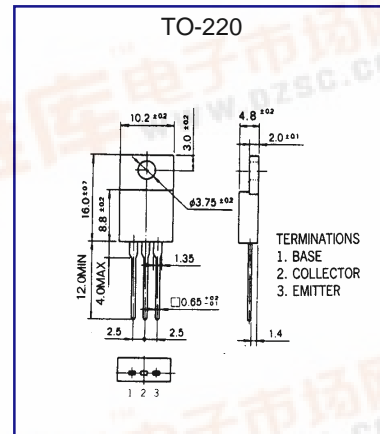




BU406/406H/408

NPN EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE SWITCHING USE IN HORIZONTAL DEFLECTION OUTPUT STAGE



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	400	V
Collector-Emitter Voltage	V _{CE0}	200	V
Emitter-Base voltage	V _{EB0}	6	V
Collector Current (DC)	I _C	7	A
Collector Peak Current	I _{CM}	10	A
Base Current (DC)	I _B	4	A
Collector Dissipation (T _c =25°C)	P _C	60	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-65~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit	
Collector Cutoff Current (V _{BE} =0)	I _{CES}	V _{CE} = 400V, V _{EB} =0			5	mA	
		V _{CE} = 250V, V _{EB} =0			100	µA	
		V _{CE} = 250V, V _{EB} =0			1	mA	
Emitter Cutoff Current (I _C =0)	I _{EBO}	V _{CE} = 250V, V _{EB} =0			1	mA	
Collector Emitter Saturation Voltage :BU406	V _{CE(sat)}	T _c =150			1	V	
		:BU406H			1	V	
		:BU408			1	V	
Base- Emitter Saturation Voltage	V _{BE(sat)}	V _{CE} = 6V, I _C =0			1	V	
		:BU406, I _C =5A, I _B =0.5A			1.2	V	
		:BU406H, I _C =5A, I _B =0.8A			1.2	V	
:BU408		I _C =6A, I _B =1.2A			1.5	V	
		Current Gain Bandwidth Product	f _T	I _C =5A, I _B =0.5A	10		MHZ
		Turn-Off Time	t _{off}	I _C =5A, I _B =0.8A			0.75
:BU406H, I _C =6A, I _B =1.2A					0.4	µS	
:BU408, V _{CE} = 10V, I _C =500mA					0.4	µS	
		I _C =5A, I _B =0.5A					
		I _C =5A, I _B =0.8A					
		I _C =6A, I _B =1.2A					

